

# MC74VHCT245A

## Octal Bus Transceiver

The MC74VHCT245A is an advanced high speed CMOS octal bus transceiver fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

It is intended for two-way asynchronous communication between data buses. The direction of data transmission is determined by the level of the DIR input. The output enable pin ( $\overline{OE}$ ) can be used to disable the device, so that the buses are effectively isolated.

All inputs are equipped with protection circuits against static discharge.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The VHCT245A input and output (when disabled) structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. These input and output structures help prevent device destruction caused by supply voltage–input/output voltage mismatch, battery backup, hot insertion, etc.

### Features

- High Speed:  $t_{PD} = 4.9$  ns (Typ) at  $V_{CC} = 5.0$  V
- Low Power Dissipation:  $I_{CC} = 4$   $\mu$ A (Max) at  $T_A = 25^\circ$ C
- TTL-Compatible Inputs:  $V_{IL} = 0.8$  V;  $V_{IH} = 2.0$  V
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Designed for 4.5 V to 5.5 V Operating Range
- Low Noise:  $V_{OLP} = 1.6$  V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:
  - Human Body Model > 2000 V;
  - Machine Model > 200 V
- Chip Complexity: 304 FETs or 76 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant

### APPLICATION NOTES

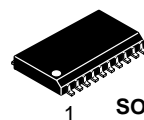
- Do not force a signal on an I/O pin when it is an active output, damage may occur.
- All floating (high impedance) input or I/O pins must be fixed by means of pullup or pulldown resistors or bus terminator ICs.



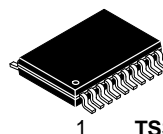
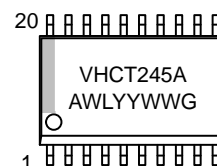
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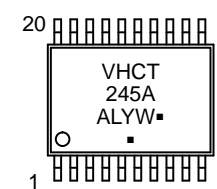
### MARKING DIAGRAMS



SOIC-20WB  
SUFFIX DW  
CASE 751D



TSSOP-20  
SUFFIX DT  
CASE 948E



A = Assembly Location  
WL, L = Wafer Lot  
YY, Y = Year  
WW, W = Work Week  
G or ▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

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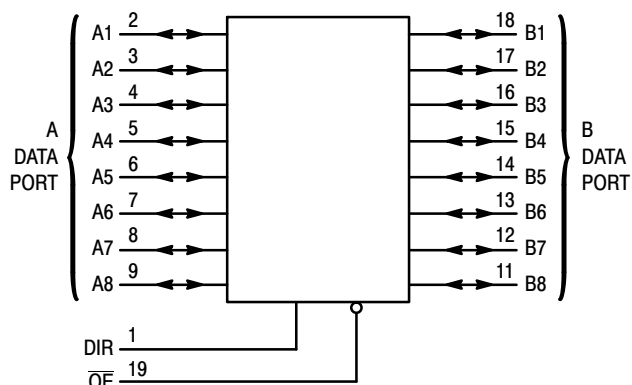


Figure 1. Logic Diagram

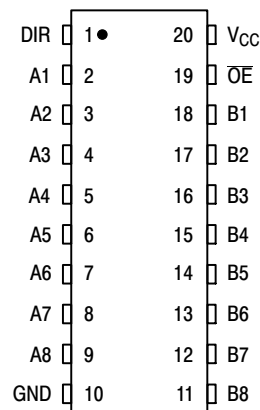


Figure 2. Pin Assignment

## FUNCTION TABLE

Control Inputs		Operation
OE	DIR	
L	L	Data Tx from Bus B to Bus A
L	H	Data Tx from Bus A to Bus B
H	X	Buses Isolated (High-Z State)

## MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CC}$	DC Supply Voltage	- 0.5 to + 7.0	V
$V_{in}$	DC Input Voltage	- 0.5 to + 7.0	V
$V_{I/O}$	DC Output Voltage	Outputs in 3-State High or Low State - 0.5 to + 7.0 - 0.5 to $V_{CC} + 0.5$	V
$I_{IK}$	Input Diode Current	- 20	mA
$I_{OK}$	Output Diode Current ( $V_{OUT} < GND$ ; $V_{OUT} > V_{CC}$ )	$\pm 20$	mA
$I_{out}$	DC Output Current, per Pin	$\pm 25$	mA
$I_{CC}$	DC Supply Current, $V_{CC}$ and GND Pins	$\pm 75$	mA
$P_D$	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
$T_{stg}$	Storage Temperature	- 65 to + 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating - SOIC Package: - 7 mW/°C from 65° to 125°C  
TSSOP Package: - 6.1 mW/°C from 65° to 125°C

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
$V_{CC}$	DC Supply Voltage	4.5	5.5	V
$V_{in}$	DC Input Voltage	0	5.5	V
$V_{I/O}$	DC Output Voltage	0	5.5	V
	Outputs in 3-State High or Low State	0	$V_{CC}$	
$T_A$	Operating Temperature	- 40	+ 85	°C
$t_r, t_f$	Input Rise and Fall Time	$V_{CC} = 5.0V \pm 0.5V$		ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$ . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

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## DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	T <sub>A</sub> = 25°C			T <sub>A</sub> = -40 to 85°C		Unit
				Min	Typ	Max	Min	Max	
V <sub>IH</sub>	Minimum High-Level Input Voltage		4.5 to 5.5	2.0			2.0		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		4.5 to 5.5			0.8		0.8	V
V <sub>OH</sub>	Minimum High-Level Output Voltage V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -50μA	4.5	4.4	4.5		4.4		V
		I <sub>OH</sub> = -8mA	4.5	3.94			3.80		
V <sub>OL</sub>	Maximum Low-Level Output Voltage V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> = 50μA	4.5		0.0	0.1		0.1	V
		I <sub>OL</sub> = 8mA	4.5			0.36		0.44	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0	μA
I <sub>OZ</sub>	Maximum 3-State Leakage Current	V <sub>in</sub> = V <sub>IL</sub> or V <sub>IH</sub> V <sub>out</sub> = V <sub>CC</sub> or GND	5.5			± 0.25		± 2.5	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5			4.0		40.0	μA
I <sub>CCT</sub>	Quiescent Supply Current	Per Input: V <sub>IN</sub> = 3.4V Other Input: V <sub>CC</sub> or GND	5.5			1.35		1.50	mA
I <sub>OPD</sub>	Output Leakage Current	V <sub>OUT</sub> = 5.5V	0			0.5		5.0	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## AC ELECTRICAL CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3.0ns)

Symbol	Parameter	Test Conditions	T <sub>A</sub> = 25°C			T <sub>A</sub> = -40 to 85°C		Unit
			Min	Typ	Max	Min	Max	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay A to B or B to A	V <sub>CC</sub> = 5.0 ± 0.5V C <sub>L</sub> = 15pF C <sub>L</sub> = 50pF		4.9 5.4	7.7 8.7	1.0 1.0	8.5 9.5	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Output Enable Time OE to A or B	V <sub>CC</sub> = 5.0 ± 0.5V R <sub>L</sub> = 1kΩ C <sub>L</sub> = 50pF		9.4 9.9	13.8 14.8	1.0 1.0	15.0 16.0	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Output Disable Time OE to A or B	V <sub>CC</sub> = 5.0 ± 0.5V R <sub>L</sub> = 1kΩ C <sub>L</sub> = 50pF		10.1	15.4	1.0	16.5	ns
t <sub>OSLH</sub> , t <sub>OSHL</sub>	Output to Output Skew	V <sub>CC</sub> = 5.0 ± 0.5V C <sub>L</sub> = 50pF (Note 1)			1.0		1.0	ns
C <sub>in</sub>	Maximum Input Capacitance			4	10		10	pF
C <sub>out</sub>	Maximum 3-State Output Capacitance (Output in High-Impedance State)			13				pF

C <sub>PD</sub>	Power Dissipation Capacitance (Note 2)	Typical @ 25°C, V <sub>CC</sub> = 5.0V		pF
		Min	Max	
			16	

- Parameter guaranteed by design. t<sub>OSLH</sub> = |t<sub>PLHm</sub> - t<sub>PLHn</sub>|, t<sub>OSHL</sub> = |t<sub>PHLm</sub> - t<sub>PHLn</sub>|.
- C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/8 (per bit). C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

## NOISE CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3.0ns, C<sub>L</sub> = 50pF, V<sub>CC</sub> = 5.0V)

Symbol	Parameter	T <sub>A</sub> = 25°C		Unit
		Typ	Max	
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	1.2	1.6	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-1.2	-1.6	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		2.0	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		0.8	V

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## ORDERING INFORMATION

Device	Package	Shipping†
MC74VHCT245ADWG	SOIC-20WB (Pb-Free)	38 Units / Rail
MC74VHCT245ADWRG	SOIC-20WB (Pb-Free)	1000 / Tape & Reel
MC74VHCT245ADTG	TSSOP-20 (Pb-Free)	75 Units / Rail
MC74VHCT245ADTRG	TSSOP-20 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

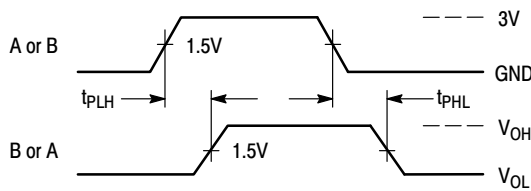


Figure 3. Switching Waveform

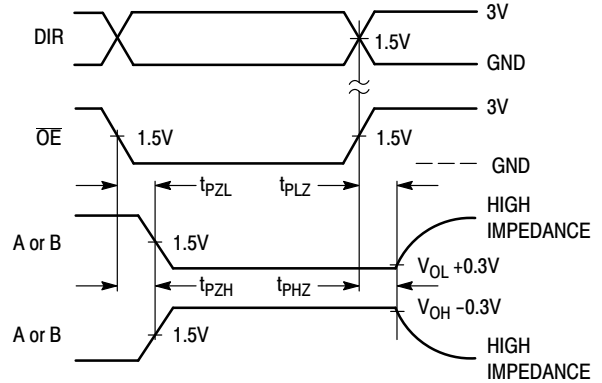
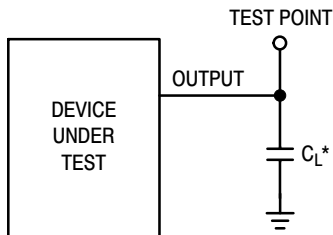
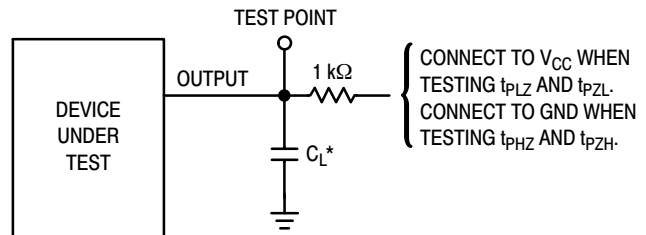


Figure 4. Switching Waveform



\*Includes all probe and jig capacitance

Figure 5. Test Circuit



\*Includes all probe and jig capacitance

Figure 6. Test Circuit

# MC74VHCT245A

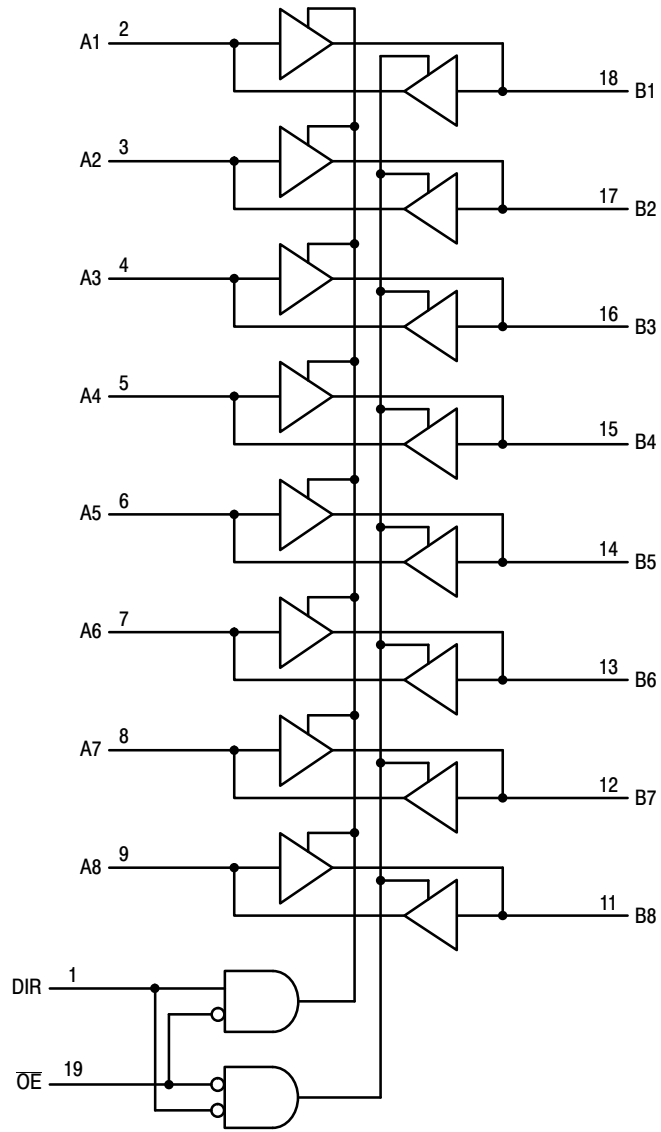
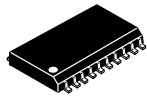


Figure 7. Expanded Logic Diagram

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

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SCALE 1:1

SOIC-20 WB  
CASE 751D-05  
ISSUE H

DATE 22 APR 2015

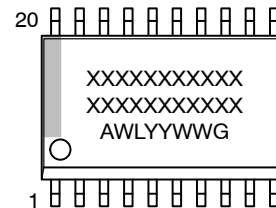


NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

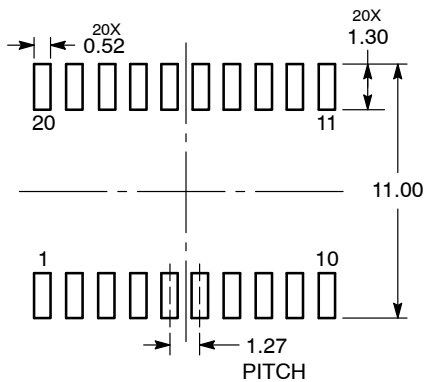
DIM	MILLIMETERS	
	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
b	0.35	0.49
c	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0°	7°

### GENERIC MARKING DIAGRAM\*



- XXXXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- YY = Year
- WW = Work Week
- G = Pb-Free Package

### RECOMMENDED SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



TSSOP-20 WB  
CASE 948E  
ISSUE D

DATE 17 FEB 2016

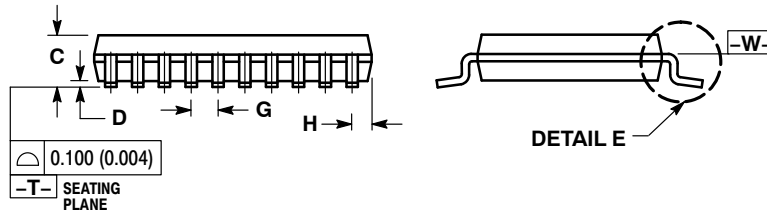
SCALE 2:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°



SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM\*



- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

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